COPY OF PAPERS
ORIGINALLY FILED

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	TRW DOCKET NO. 12-1120	SERIAL NO. 09/840,600
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	APPLICANT: Roger S. Tsai	
	FILING DATE: April 23, 2001	GROUP: 2858

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
TT		5 9 7 6 9 2 0	11/2/99	Kenichi Nakano, et al.	—	—	
TT		6 2 1 7 2 1 0	4/17/01	Robert S. Roeder, et al.	—	—	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

TT		Ramakrishna, S., et al., *HEMT Modelling Using Semi-Physical Expressions for the Equilibrium Space-Charge Parameters of the Modulation-Doped Heterojunction,* IEEE, August 1999, pgs. 211-214.
TT		Winson, Peter B., et al., *A Table Based Bias and Temperature Dependent Small Signal and Noise Equivalent Circuit Model,* IEEE, May 1995, pgs. 623-626, entire document.
TT		Karmalkar, Shreepad, et al., *A Simple Yet Comprehensive Unified Physical Model of the 2-D Electron Gas in Delta-Doped and Uniformly Doped High Electron Mobility Transistors,* IEEE, Vol. 47, No. 1, January 2000, pgs. 11-23.
TT		Francois Danneville, et al., *Noise Modeling in MESFET and HEMT Mixers Using a Uniform Noisy Line Model,* IEEE, Vol. 45, No. 10, October 1998, pgs. 2207-2212.
TT		Ranjit Singh, et al., *Small-Signal Characterization of Microwave and Millimeter-Wave HEMT's Based on a Physical Model,* IEEE, Vol. 44, No. 1, January 1996, pgs. 114-121.

EXAMINER	DATE CONSIDERED
Thien Tran	12-11-02

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw lin through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.